Rev A.1.1

DESCRIPTION:

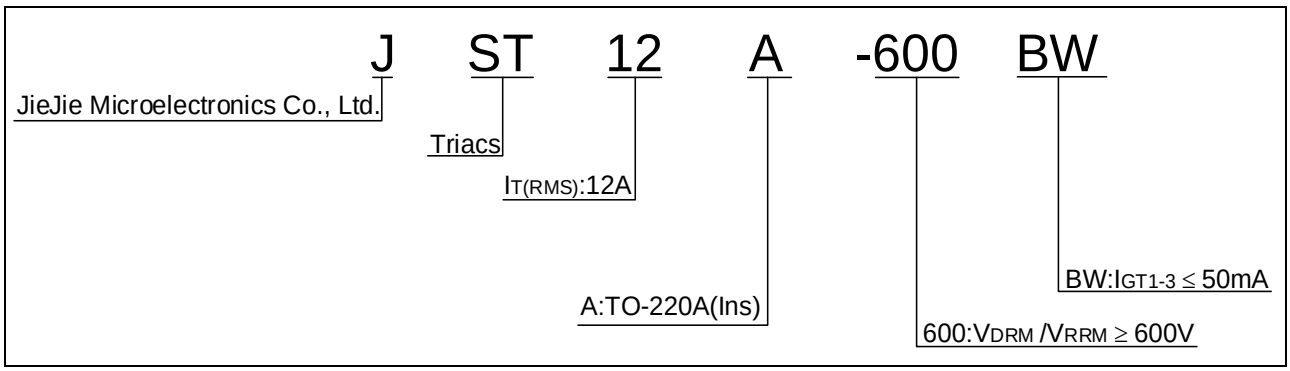
The JST12A1-600, BW)4 (pos)14298 60(-)T1IOW tChi8 (orng 0 Td. -32 I -32) -32 tan b0 Td [M9

Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	4.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	70	mA
				90	
I_H	I_T =500mA			05<</MCID 61 >>BDC 0.004 Tc -0.004 Tw 6	

ORDERING INFORMATION



MARKING

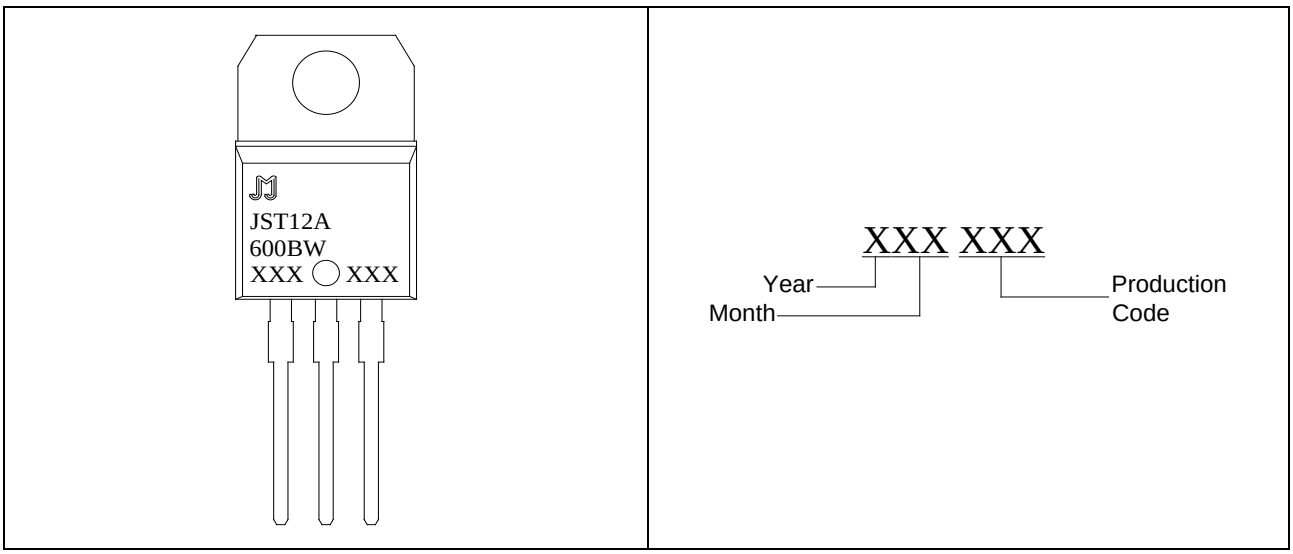


FIG.1: Maximum power dissipation versus RMS on-state current

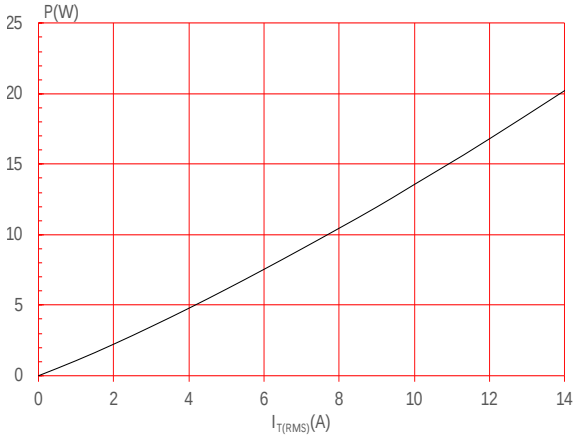


FIG.2: RMS on-state current versus case temperature

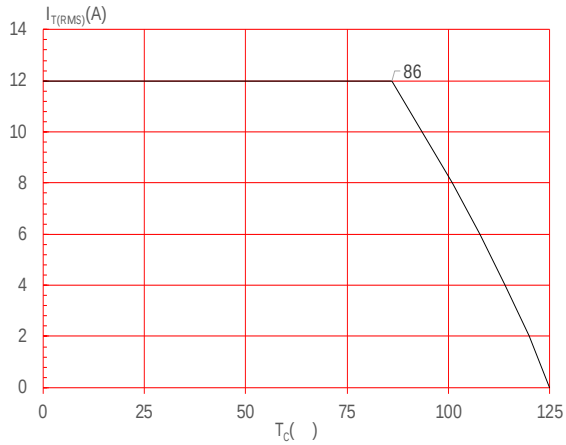


FIG.3: Surge peak on-state current versus number of cycles

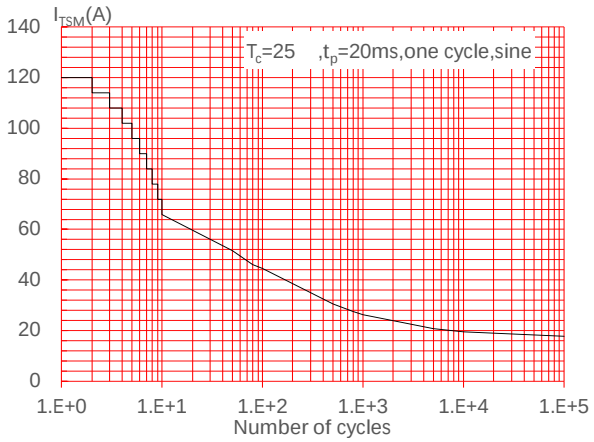


FIG.4: On-state characteristics

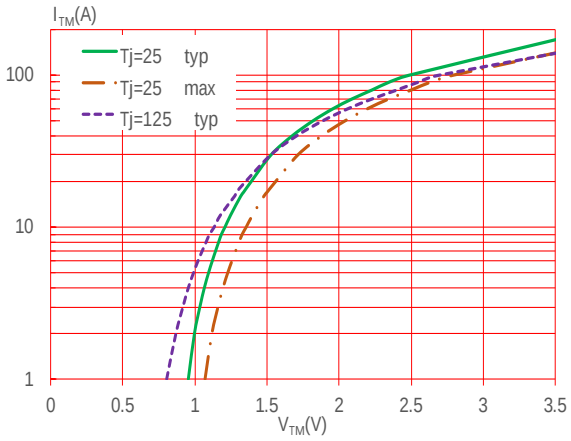


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width t_p<20ms, and corresponding value of I^2t (dI/dt<100A/μs)

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

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